

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

IPA65R190C7

| FEATUR With TO Low inpute Reduced 100% average Minimum performant APPLIC Switching | 1 2 3 | | | D(2) G(1) S(3) pin 1, Gate 2, Drain 3. Source TO-220F package | | | | | |
|---|--|-----|------|---|-----------------------|----------------------|----------------------|----------------------|----|
| • ABSOL | UTE MAXIMUM RATINGS(Ta=25°C) | ► B | ġ | | 0 | ⊕ ¢'i | | | |
| SYMBOL | PARAMETER | VAL | UE | UNIT | FOC | | 5 | ÷- | A |
| V _{DSS} | Drain-Source Voltage | 65 | 50 | V | | | | ÷ L | |
| V _{GSS} | Gate-Source Voltage | ±: | 30 | V | L-+;;-(,) | ÷. | + R - | | |
| Ι _D | Drain Current-Continuous @Tc=25℃ (V _{GS} at 10V) Tc=100℃ | 8 | | A | | ĸ | | | |
| I _{DM} | Drain Current-Single Pulsed | 4 | 9 | А | D | | J | Ļ | ųų |
| PD | Total Dissipation @T _c =25℃ | 3 | 0 | W | | DIM | - | m MAX |] |
| Tj | Max. Operating Junction Temperature | 15 | 50 | °C | | AB | 14.95 | 15.05 | - |
| T _{stg} | Storage Temperature -5 | | 150 | °C | | C D F | 4.40 0.75 3.10 | 4.60 0.90 3.30 | - |
| • THERM | AL CHARACTERISTICS | | | | | H J | 3.70 | 3.90 0.70 | |
| SYMBOL | PARAMETER | | МАХ | UNIT | - | K | 13.4 1.10 | 13.6 1.30 | - |
| Rth(ch-c) | Channel-to-case thermal resistance | | 4.21 | °C/W | - | N Q | 5.00 | 5.20 | |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 80 | °C/W | _ | R S U | 2.20 2.65 6.40 | 2.40 2.90 6.60 | - | |
| isc webs | ite: www.iscsemi.cn | 1 | is | c & iscs | e <i>mi</i> is regist | erec | d trade | emark | |



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ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|---------------------|--------------------------------|--|-----|-----|----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =1mA | 650 | | | v |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =0.29mA | 3.0 | | 4.0 | v |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =5.7A | | 168 | 190 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±20V;V _{DS} = 0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 650V; V _{GS} = 0V;Tj=25℃ V _{DS} = 650V; V _{GS} = 0V; Tj=150℃ | | | 1 100 | μ Α |
| V _{SDF} | Diode forward voltage | I _{SD} =5.7A, V _{GS} = 0V | | 0.9 | | V |

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